

LM7301低消費電力、4MHz GBW、SOT-23パッケージ、 レール・ツー・レール入出力オペアンプ

1 特長

- $V_S = 5V$ について(特に記載のない限り標準値)
- 5ピンのSOT-23パッケージにより省スペースが可能
- レール・ツー・レールより大きな入力CMVR:
-0.25V~5.2V
- レール・ツー・レール出力スイング:
0.07V~4.93V
- 広いゲイン帯域幅: 4MHz
- 低消費電流: 0.6mA
- 広い電源電圧範囲: 1.8V~32V
- 高いPSRR: 104dB
- 高いCMRR: 93dB
- 非常に優れたゲイン: 97dB

2 アプリケーション

- 携帯機器
- 信号コンディショニング・アンプ/ADCバッファ
- アクティブ・フィルタ
- モデム
- PCMCIAカード

3 概要

LM7301は広範なアプリケーションで高い性能を提供します。LM7301には、レール・ツー・レールより大きな入力範囲、レール・ツー・レール出力スイング、大きな容量性負荷の駆動能力、低い歪みといった特長があります。

このデバイスは、わずか0.6mAの消費電流で4MHzのゲイン帯域幅動作が可能です。大電力のデバイスではバッテリーの消耗が激しくて使用できないような、新しいポータブル・アプリケーションをサポートできます。

LM7301は両方の電源レールを超える電圧で駆動可能なため、同相モードの電圧範囲を超過する懸念がなくなります。レール・ツー・レール出力スイングにより、出力において最大のダイナミック・レンジが得られます。低い電源電圧で動作するとき、これは特に重要な機能です。

LM7301は1.8V~32Vの電源で動作し、低消費電力システムで機能する多くのアプリケーションに優れた性能を示します。

信号源のすぐ近くにアンプを配置することで、基板サイズ削減と、信号の伝送経路の簡素化を実現できます。

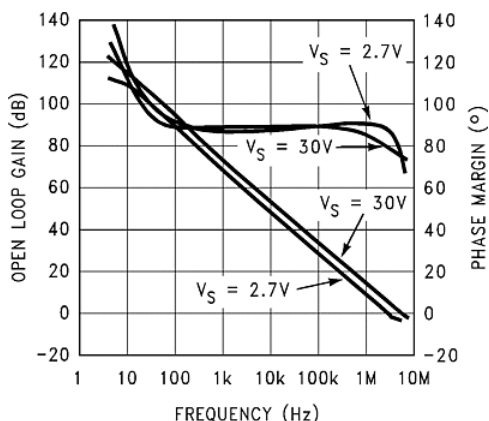
LM7301は、薄型形状のPCMCIAカードに容易に適合します。

製品情報⁽¹⁾

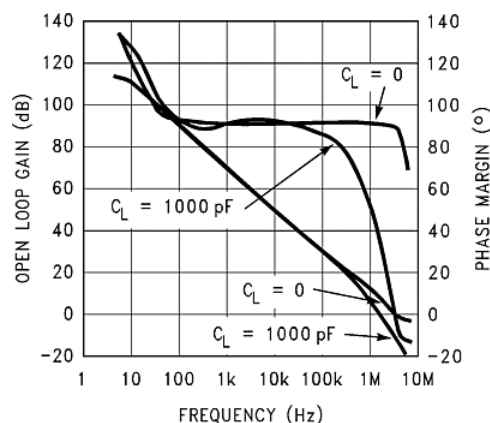
型番	パッケージ	本体サイズ(公称)
LM7301	SOIC (8)	4.90mm×3.91mm
	SOT-23 (5)	2.90mm×1.60mm

(1) 提供されているすべてのパッケージについては、巻末の注文情報を参照してください。

ゲインと位相



ゲインと位相、2.7V電源



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4 改訂履歴

資料番号末尾の英字は改訂を表しています。その改訂履歴は英語版に準じています。

Revision H (March 2013) から Revision I に変更

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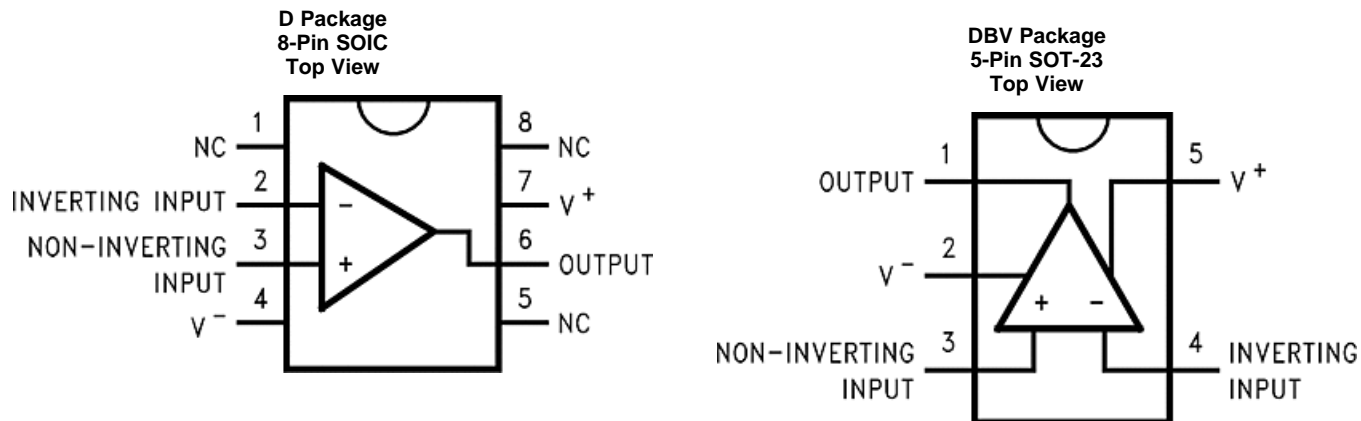
• 「ESD定格」の表、「機能説明」セクション、「デバイスの機能モード」セクション、「アプリケーションと実装」セクション、「電源に関する推奨事項」セクション、「レイアウト」セクション、「デバイスおよびドキュメントのサポート」セクション、「メカニカル、パッケージ、および注文情報」セクション 追加	1
• Changed 58°C to 42°C in <i>Power Dissipation</i>	15
• Changed 113°C to 59°C in <i>Power Dissipation</i>	15
• Changed 29°C to 21°C in <i>Power Dissipation</i>	15
• Changed 57°C to 30°C in <i>Power Dissipation</i>	15

Revision G (March 2013) から Revision H に変更

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• Changed layout of National Semiconductor Data Sheet to TI format	16
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5 Pin Configuration and Functions



Pin Functions

NAME	PIN		I/O	DESCRIPTION
	SOIC	SOT-23		
-IN	2	4	I	Inverting input voltage
+IN	3	3	I	Noninverting input voltage
N/C	1, 5, 8	—	—	No connection
OUT	6	1	O	Output
V ⁻	4	2	I	Negative supply
V ⁺	7	5	I	Positive supply

6 Specifications

6.1 Absolute Maximum Ratings

over operating free-air temperature range (unless otherwise noted)⁽¹⁾⁽²⁾

	MIN	MAX	UNIT
Differential input voltage		15	V
Voltage at input and output pin	(V ⁺) + 0.3	(V ⁻) – 0.3	V
Supply voltage (V ⁺ – V ⁻)		35	V
Current at input pin		±10	mA
Current at output pin ⁽³⁾		±20	mA
Current at power supply pin		25	mA
Junction temperature, T _J ⁽⁴⁾		150	°C
Storage temperature, T _{stg}	–65	150	°C

- (1) Stresses beyond those listed under *Absolute Maximum Ratings* may cause permanent damage to the device. These are stress ratings only, which do not imply functional operation of the device at these or any other conditions beyond those indicated under *Recommended Operating Conditions*. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.
- (2) If Military/Aerospace specified devices are required, contact the Texas Instruments Sales Office/Distributors for availability and specifications.
- (3) Applies to both single-supply and split-supply operation. Continuous short-circuit operation at elevated ambient temperature can result in exceeding the maximum allowed junction temperature of 150°C.
- (4) The maximum power dissipation is a function of T_{J(MAX)}, R_{θJA}, and T_A. The maximum allowable power dissipation at any ambient temperature is P_D = (T_{J(MAX)} – T_A)/R_{θJA}. All numbers apply for packages soldered directly into a PC board.

6.2 ESD Ratings

	VALUE	UNIT
V _(ESD) Electrostatic discharge	Human-body model (HBM), per ANSI/ESDA/JEDEC JS-001 ⁽¹⁾	±2500 V

- (1) JEDEC document JEP155 states that 2500-V HBM allows safe manufacturing with a standard ESD control process.

6.3 Recommended Operating Conditions

over operating free-air temperature range (unless otherwise noted)⁽¹⁾

	MIN	NOM	MAX	UNIT
Supply voltage	1.8		32	V
Operating temperature ⁽²⁾	–40		85	°C
Package thermal resistance (R _{θJA}) ⁽²⁾	5-pin SOT-23	325	325	°C/W
	8-pin SOIC	165	165	°C/W

- (1) Absolute Maximum Ratings indicate limits beyond which damage to the device may occur. Operating Ratings indicate conditions for which the device is intended to be functional, but specific performance is not ensured. For ensured specifications and the test conditions, see the Electrical Characteristics.
- (2) The maximum power dissipation is a function of T_{J(MAX)}, R_{θJA}, and T_A. The maximum allowable power dissipation at any ambient temperature is P_D = (T_{J(MAX)} – T_A)/R_{θJA}. All numbers apply for packages soldered directly into a PC board.

6.4 Thermal Information

THERMAL METRIC ⁽¹⁾	LM7301		UNIT
	DBV (SOT-23)	D (SOIC)	
	5 PINS	8 PINS	
R _{θJA} Junction-to-ambient thermal resistance	169	120	°C/W
R _{θJC(top)} Junction-to-case (top) thermal resistance	122	65	°C/W
R _{θJB} Junction-to-board thermal resistance	30	61	°C/W
ψ _{JT} Junction-to-top characterization parameter	17	16	°C/W
ψ _{JB} Junction-to-board characterization parameter	29	60	°C/W
R _{θJC(bot)} Junction-to-case (bottom) thermal resistance	N/A	N/A	°C/W

- (1) For more information about traditional and new thermal metrics, see the *Semiconductor and IC Package Thermal Metrics* application report, [SPRA953](#).

6.5 Electrical Characteristics: 5-V DC

Unless otherwise specified, all limits ensured for $T_A = 25^\circ\text{C}$, $V^+ = 5\text{V}$, $V^- = 0\text{V}$, $V_{\text{CM}} = V_O = V^+/2$ and $R_L > 1\text{M}\Omega$ to $V^+/2$ unless noted that limits apply at the temperature extremes.^{(1) (2)(3)}

PARAMETER		TEST CONDITIONS		MIN	TYP	MAX	UNIT
V_{OS}	Input offset voltage	$T_A = 25^\circ\text{C}$			0.03	6	mV
		$T_A = T_J$				8	
TCV_{OS}	Input offset voltage average drift	$T_A = T_J$			2		$\mu\text{V}/^\circ\text{C}$
I_B	Input bias current	$V_{\text{CM}} = 0\text{V}$	$T_A = 25^\circ\text{C}$		90	200	nA
			$T_A = T_J$			250	
		$V_{\text{CM}} = 5\text{V}$	$T_A = 25^\circ\text{C}$		-40	-75	
			$T_A = T_J$			-85	
I_{OS}	Input offset current	$V_{\text{CM}} = 0\text{V}$	$T_A = 25^\circ\text{C}$		0.7	70	nA
			$T_A = T_J$			80	
		$V_{\text{CM}} = 5\text{V}$	$T_A = 25^\circ\text{C}$		0.7	55	
			$T_A = T_J$			65	
R_{IN}	Input resistance, CM	$0\text{V} \leq V_{\text{CM}} \leq 5\text{V}$			39		$\text{M}\Omega$
CMRR	Common mode rejection ratio	$0\text{V} \leq V_{\text{CM}} \leq 5\text{V}$	$T_A = 25^\circ\text{C}$	70	88		dB
			$T_A = T_J$	67			
		$0\text{V} \leq V_{\text{CM}} \leq 3.5\text{V}$		93			
PSRR	Power supply rejection ratio	$2.2\text{V} \leq V^+ \leq 30\text{V}$	$T_A = 25^\circ\text{C}$	87	104		dB
			$T_A = T_J$	84			
V_{CM}	Input common-mode voltage range	$\text{CMRR} \geq 65\text{dB}$			5.1		V
					-0.1		
A_V	Large signal voltage gain	$R_L = 10\text{k}\Omega$ $V_O = 4\text{V}_{\text{PP}}$	$T_A = 25^\circ\text{C}$	14	71		V/mV
			$T_A = T_J$	10			
V_O	Output swing	$R_L = 10\text{k}\Omega$	$T_A = 25^\circ\text{C}$		0.07	0.12	V
					4.93		
			$T_A = T_J$		4.88	0.15	
					4.85		
		$R_L = 2\text{k}\Omega$	$T_A = 25^\circ\text{C}$		0.14	0.2	
						0.22	
$T_A = T_J$		4.80	4.87				
		4.78					
I_{SC}	Output short-circuit current	Sourcing	$T_A = 25^\circ\text{C}$	8	11		mA
			$T_A = T_J$	5.5			
		Sinking	$T_A = 25^\circ\text{C}$	6	9.5		
			$T_A = T_J$	5			
I_S	Supply current	$T_A = 25^\circ\text{C}$			0.6	1.1	mA
		$T_A = T_J$				1.24	

- (1) All limits are ensured by testing or statistical analysis.
- (2) Typical values represent the most likely parametric norm as determined at the time of characterization. Actual typical values may vary over time and will also depend on the application and configuration. The typical values are not tested and are not ensured on shipped production material.
- (3) Electrical Table values apply only for factory testing conditions at the temperature indicated. Factory testing conditions result in very limited self-heating of the devices such that $T_J = T_A$. No ensure of parametric performance is indicated in the electrical tables under conditions of internal self-heating where $T_J > T_A$.

6.6 Electrical Characteristics: AC

 $T_A = 25^\circ\text{C}$, $V^+ = 2.2\text{ V to }30\text{ V}$, $V^- = 0\text{ V}$, $V_{CM} = V_O = V^+/2$ and $R_L > 1\text{ M}\Omega$ to $V^+/2$ ⁽¹⁾

PARAMETER		TEST CONDITIONS	TYP ⁽²⁾	UNIT
SR	Slew rate	$\pm 4\text{-V Step at }V_S \pm 6\text{ V}$	1.25	V/ μs
GBW	Gain-bandwidth product	$f = 100\text{ kHz}$, $R_L = 10\text{ k}\Omega$	4	MHz
e_n	Input-referred voltage noise	$f = 1\text{ kHz}$	36	nV/ $\sqrt{\text{Hz}}$
i_n	Input-referred current noise	$f = 1\text{ kHz}$	0.24	pA/ $\sqrt{\text{Hz}}$
T.H.D.	Total harmonic distortion	$f = 10\text{ kHz}$	0.006%	

- (1) Electrical Table values apply only for factory testing conditions at the temperature indicated. Factory testing conditions result in very limited self-heating of the devices such that $T_J = T_A$. No ensure of parametric performance is indicated in the electrical tables under conditions of internal self-heating where $T_J > T_A$.
- (2) Typical values represent the most likely parametric norm as determined at the time of characterization. Actual typical values may vary over time and will also depend on the application and configuration. The typical values are not tested and are not ensured on shipped production material.

6.7 Electrical Characteristics: 2.2-V DC

 Unless otherwise specified, all limits ensured for $T_A = 25^\circ\text{C}$, $V^+ = 2.2\text{ V}$, $V^- = 0\text{ V}$, $V_{CM} = V_O = V^+/2$ and $R_L > 1\text{ M}\Omega$ to $V^+/2$ unless noted that limits apply at the temperature.⁽¹⁾⁽²⁾

PARAMETER		TEST CONDITIONS		MIN	TYP	MAX	UNIT
V_{OS}	Input offset voltage	$T_A = 25^\circ\text{C}$			0.04	6	mV
		$T_A = T_J$				8	
TCV_{OS}	Input offset voltage average drift	$T_A = T_J$			2		$\mu\text{V}/^\circ\text{C}$
I_B	Input bias current	$V_{CM} = 0\text{ V}$	$T_A = 25^\circ\text{C}$		89	200	nA
			$T_A = T_J$			250	
		$V_{CM} = 2.2\text{ V}$	$T_A = 25^\circ\text{C}$	-75	-35		
			$T_A = T_J$	-85			
I_{OS}	Input offset current	$V_{CM} = 0\text{ V}$	$T_A = 25^\circ\text{C}$		0.8	70	nA
			$T_A = T_J$			80	
		$V_{CM} = 2.2\text{ V}$	$T_A = 25^\circ\text{C}$		0.4	55	
			$T_A = T_J$			65	
R_{IN}	Input resistance	$0\text{ V} \leq V_{CM} \leq 2.2\text{ V}$			18		M Ω
CMRR	Common-mode rejection ratio	$0\text{ V} \leq V_{CM} \leq 2.2\text{ V}$		$T_A = 25^\circ\text{C}$	60	82	dB
				$T_A = T_J$	56		
PSRR	Power supply rejection ratio	$2.2\text{ V} \leq V^+ \leq 30\text{ V}$		$T_A = 25^\circ\text{C}$	87	104	dB
				$T_A = T_J$	84		
V_{CM}	Input common-mode voltage range	CMRR > 60 dB				2.3	V
						-0.1	
A_V	Large signal voltage gain	$R_L = 10\text{ k}\Omega$ $V_O = 1.6\text{ V}_{PP}$	$T_A = 25^\circ\text{C}$	6.5	46	V/mV	
			$T_A = T_J$	5.4			
V_O	Output swing	$R_L = 10\text{ k}\Omega$	$T_A = 25^\circ\text{C}$		0.05	0.08	V
			$T_A = T_J$			2.15	
		$R_L = 2\text{ k}\Omega$	$T_A = 25^\circ\text{C}$		0.09	0.13	
			$T_A = T_J$			0.14	

- (1) Typical values represent the most likely parametric norm as determined at the time of characterization. Actual typical values may vary over time and will also depend on the application and configuration. The typical values are not tested and are not ensured on shipped production material.
- (2) All limits are ensured by testing or statistical analysis.

Electrical Characteristics: 2.2-V DC (continued)

Unless otherwise specified, all limits ensured for $T_A = 25^\circ\text{C}$, $V^+ = 2.2\text{ V}$, $V^- = 0\text{ V}$, $V_{\text{CM}} = V_O = V^+/2$ and $R_L > 1\text{ M}\Omega$ to $V^+/2$ unless noted that limits apply at the temperature. ⁽¹⁾⁽²⁾

PARAMETER	TEST CONDITIONS		MIN	TYP	MAX	UNIT
I_{SC} Output short-circuit current	Sourcing	$T_A = 25^\circ\text{C}$	8	10.9		mA
		$T_A = T_J$	5.5			
	Sinking	$T_A = 25^\circ\text{C}$	6	7.7		
		$T_A = T_J$	5			
I_S Supply current	$T_A = 25^\circ\text{C}$			0.57	0.97	mA
	$T_A = T_J$				1.24	

6.8 Electrical Characteristics: 30-V DC

Unless otherwise specified, all limits ensured for $T_A = 25^\circ\text{C}$, $V^+ = 30\text{ V}$, $V^- = 0\text{ V}$, $V_{\text{CM}} = V_O = V^+/2$ and $R_L > 1\text{ M}\Omega$ to $V^+/2$ unless noted that limits apply at the temperature ⁽¹⁾

PARAMETER	TEST CONDITIONS		MIN	TYP	MAX	UNIT
V_{OS} Input offset voltage				0.04	6	mV
					8	
TCV_{OS} Input offset voltage average drift	$T_A = T_J$			2		$\mu\text{V}/^\circ\text{C}$
I_B Input bias current	$V_{\text{CM}} = 0\text{ V}$	$T_A = 25^\circ\text{C}$		103	300	nA
		$T_A = T_J$			500	
	$V_{\text{CM}} = 30\text{ V}$	$T_A = 25^\circ\text{C}$	-100	-50		
		$T_A = T_J$	-200			
I_{OS} Input offset current	$V_{\text{CM}} = 0\text{ V}$	$T_A = 25^\circ\text{C}$		1.2	90	nA
		$T_A = T_J$			190	
	$V_{\text{CM}} = 30\text{ V}$	$T_A = 25^\circ\text{C}$		0.5	65	
		$T_A = T_J$			135	
R_{IN} Input resistance	$0\text{ V} \leq V_{\text{CM}} \leq 30\text{ V}$			200		$\text{M}\Omega$
CMRR Common mode rejection ratio	$0\text{ V} \leq V_{\text{CM}} \leq 30\text{ V}$	$T_A = 25^\circ\text{C}$	80	104		dB
		$T_A = T_J$	78			
	$0\text{ V} \leq V_{\text{CM}} \leq 27\text{ V}$	$T_A = 25^\circ\text{C}$	90	115		
		$T_A = T_J$	88			
PSRR Power supply rejection ratio	$2.2\text{ V} \leq V^+ \leq 30\text{ V}$	$T_A = 25^\circ\text{C}$	87	104		dB
		$T_A = T_J$	84			
V_{CM} Input common-mode voltage range	$\text{CMRR} > 80\text{ dB}$			30.1		V
				-0.1		
A_V Large signal voltage gain	$R_L = 10\text{ k}\Omega$ $V_O = 28\text{ V}_{\text{PP}}$	$T_A = 25^\circ\text{C}$	30	105		V/mV
		$T_A = T_J$	20			
V_O Output swing	$R_L = 10\text{ k}\Omega$	$T_A = 25^\circ\text{C}$		0.16	0.275	V
		$T_A = T_J$			0.375	
		$T_A = 25^\circ\text{C}$	29.75	29.8		
		$T_A = T_J$	28.65			
I_{SC} Output short-circuit current	Sourcing ⁽²⁾	$T_A = 25^\circ\text{C}$	8.8	11.7		mA
		$T_A = T_J$	6.5			
	Sinking ⁽²⁾	$T_A = 25^\circ\text{C}$	8.2	11.5		
		$T_A = T_J$	6			

(1) Electrical Table values apply only for factory testing conditions at the temperature indicated. Factory testing conditions result in very limited self-heating of the devices such that $T_J = T_A$. No ensure of parametric performance is indicated in the electrical tables under conditions of internal self-heating where $T_J > T_A$.

(2) The maximum power dissipation is a function of $T_{\text{J(MAX)}}$, $R_{\theta\text{JA}}$, and T_A . The maximum allowable power dissipation at any ambient temperature is $P_D = (T_{\text{J(MAX)}} - T_A)/R_{\theta\text{JA}}$. All numbers apply for packages soldered directly into a PC board.

Electrical Characteristics: 30-V DC (continued)

Unless otherwise specified, all limits ensured for $T_A = 25^\circ\text{C}$, $V^+ = 30\text{ V}$, $V^- = 0\text{ V}$, $V_{\text{CM}} = V_O = V^+/2$ and $R_L > 1\text{ M}\Omega$ to $V^+/2$ unless noted that limits apply at the temperature⁽¹⁾

PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
I_S	Supply current	$T_A = 25^\circ\text{C}$		0.72	1.3	mA
		$T_A = T_J$			1.35	

6.9 Typical Characteristics

$T_A = 25^\circ\text{C}$, $R_L = 1\text{ M}\Omega$ unless otherwise specified

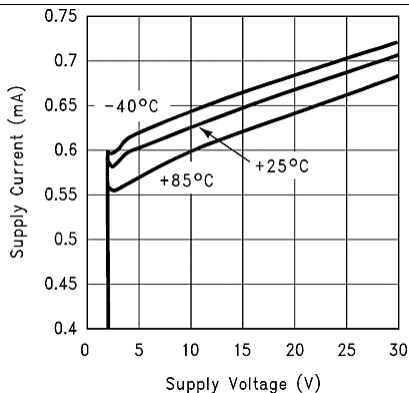


Figure 1. Supply Current vs Supply Voltage

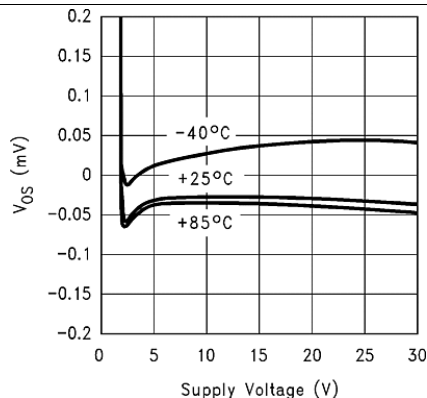


Figure 2. V_{OS} vs Supply Voltage

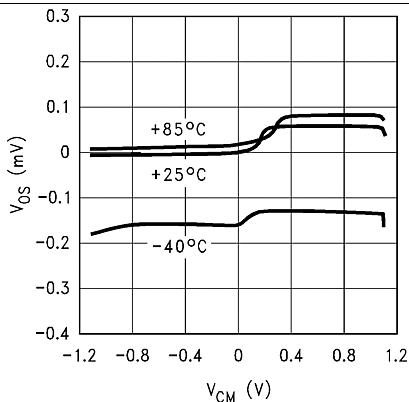


Figure 3. V_{OS} vs V_{CM} $V_S = \pm 1.1\text{ V}$

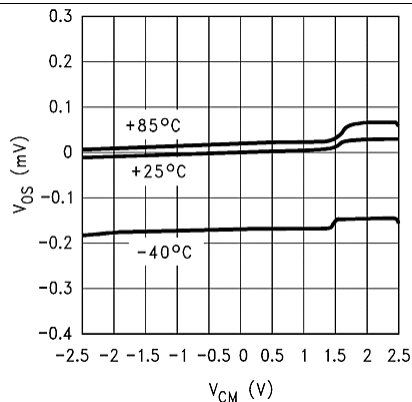


Figure 4. V_{OS} vs V_{CM} $V_S = \pm 2.5\text{ V}$

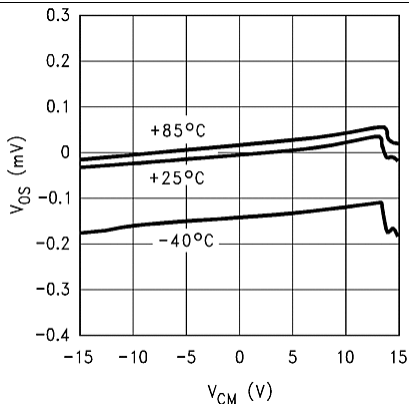


Figure 5. V_{OS} vs V_{CM} $V_S = \pm 15\text{ V}$

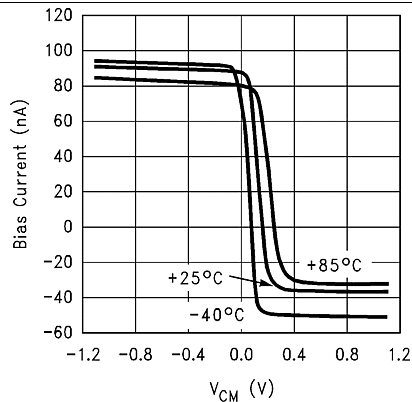


Figure 6. Inverting Input Bias Current vs Common Mode Voltage $V_S = \pm 1.1\text{ V}$

Typical Characteristics (continued)

$T_A = 25^\circ\text{C}$, $R_L = 1\text{ M}\Omega$ unless otherwise specified

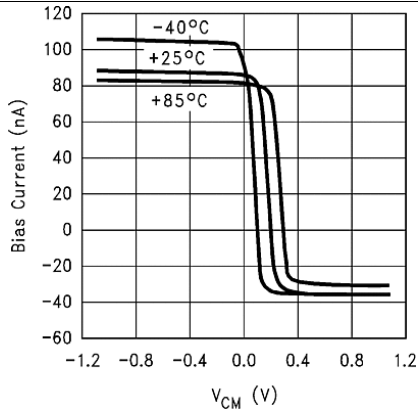


Figure 7. Noninverting Input Bias Current vs Common Mode Voltage $V_S = \pm 1.1\text{ V}$

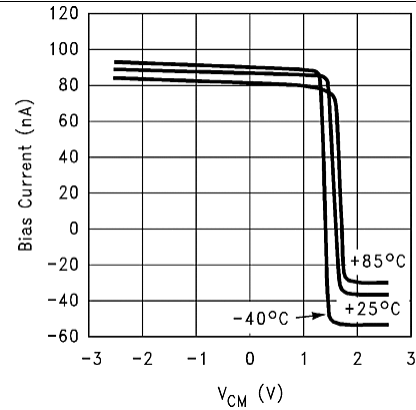


Figure 8. Inverting Input Bias Current vs Common Mode Voltage $V_S = \pm 2.5\text{ V}$

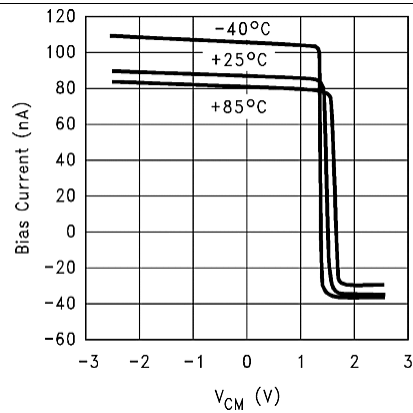


Figure 9. Noninverting Input Bias Current vs Common Mode Voltage $V_S = \pm 2.5\text{ V}$

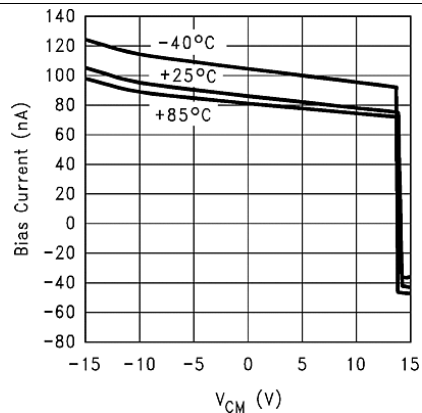


Figure 10. Noninverting Input Bias Current vs Common Mode Voltage $V_S = \pm 15\text{ V}$

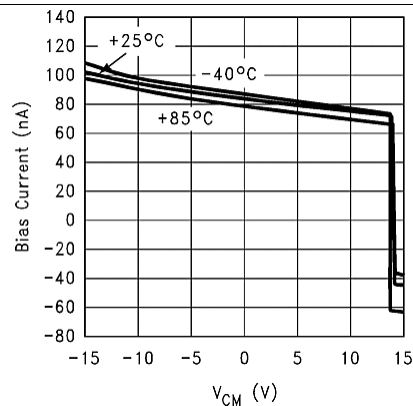


Figure 11. Inverting Input Bias Current vs Common Mode Voltage $V_S = \pm 15\text{ V}$

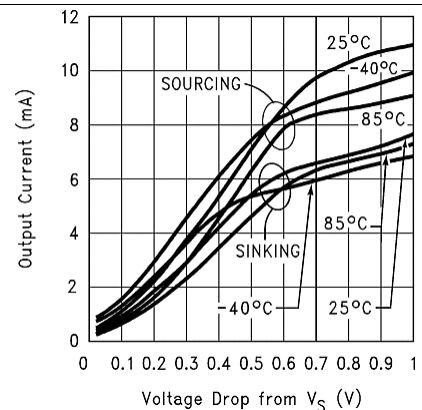


Figure 12. V_O vs I_O $V_S = \pm 1.1\text{ V}$

Typical Characteristics (continued)

$T_A = 25^\circ\text{C}$, $R_L = 1\text{ M}\Omega$ unless otherwise specified

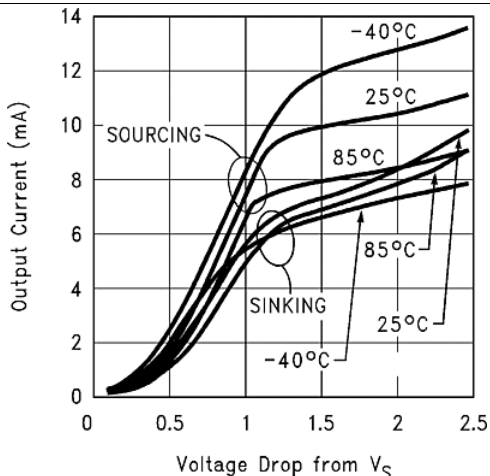


Figure 13. V_O vs I_O $V_S = \pm 2.5\text{ V}$

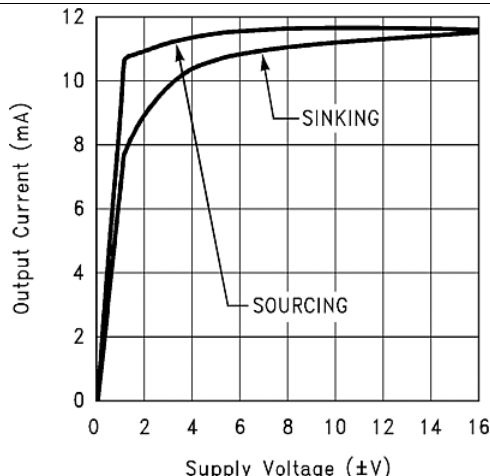


Figure 14. Short-Circuit Current vs Supply Voltage

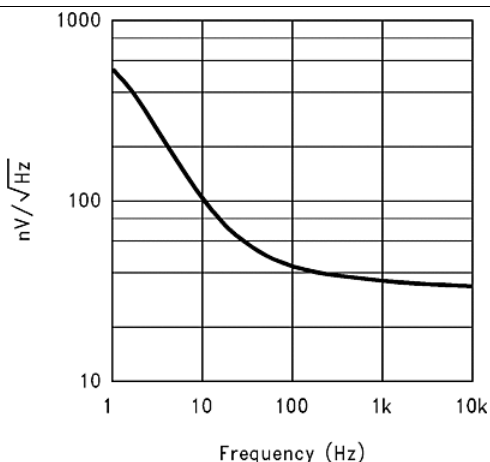


Figure 15. Voltage Noise vs Frequency

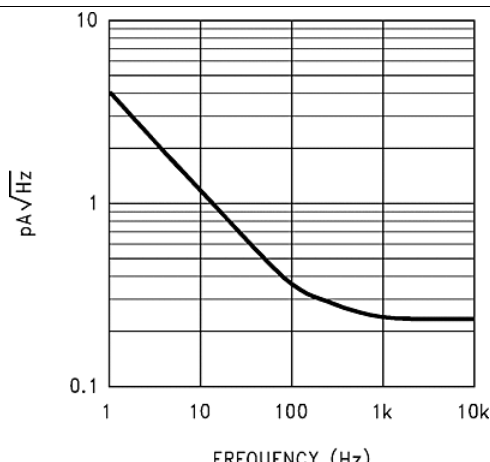


Figure 16. Current Noise vs Frequency

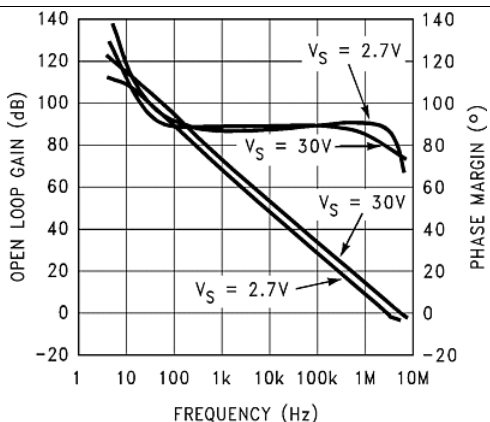


Figure 17. Gain and Phase

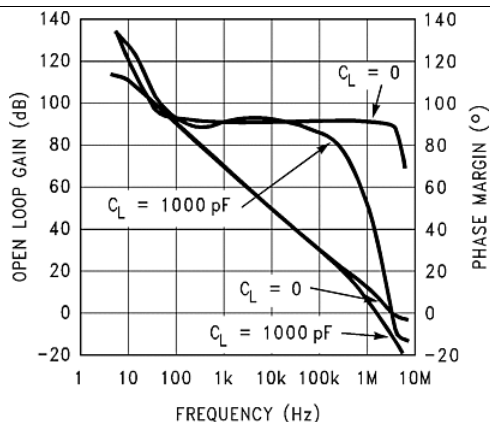


Figure 18. Gain and Phase, 2.7-V Supply

7 Detailed Description

7.1 Overview

Low supply current, wide bandwidth, input common mode voltage range that includes both rails, rail-to-rail output, good capacitive load driving ability, wide supply voltage (1.8 V to 32 V), and low distortion all make the LM7301 ideal for many diverse applications.

The high common-mode rejection ratio and full rail-to-rail input range provides precision performance when operated in noninverting applications where the common-mode error is added directly to the other system errors.

7.2 Feature Description

7.2.1 Capacitive Load Driving

The LM7301 has the ability to drive large capacitive loads. For example, 1000 pF only reduces the phase margin to about 25°.

7.2.2 Transient Response

The LM7301 offers a very clean, well-behaved transient response. [Figure 19](#), [Figure 20](#), [Figure 22](#), and [Figure 23](#) show the response when operated at gains of +1 and –1 when handling both small and large signals. The large phase margin, typically 70° to 80°, assures clean and symmetrical response. In the large signal scope photos, [Figure 19](#) and [Figure 22](#), the input signal is set to 4.8 V. The output goes to within 100 mV of the supplies cleanly and without overshoot. In the small signal samples, the response is clean, with only slight overshoot when used as a follower. [Figure 21](#) and [Figure 24](#) are the circuits used to make these photos.

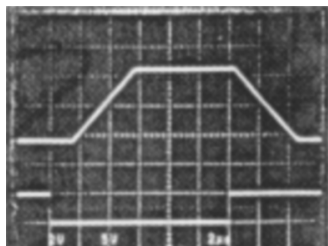


Figure 19. $A_V = -1$ V/V, Large Signal Behavior (1 V/div, 2 μ s/div)

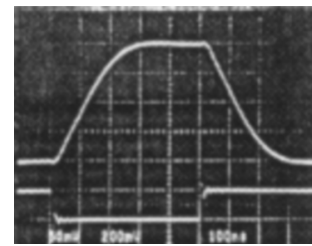
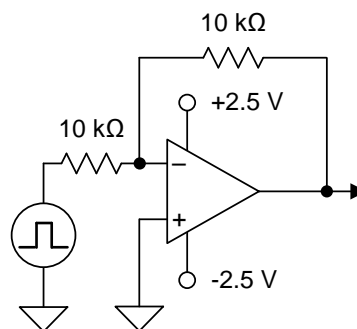


Figure 20. $A_V = -1$ V/V, Small Signal Behavior (0.2 V/div, 100 μ s/div)



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Figure 21. $A_V = -1$ V/V Schematic

Feature Description (continued)

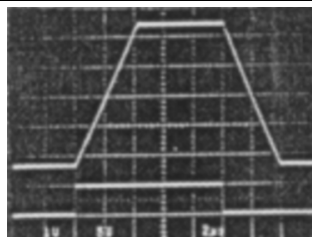


Figure 22. $A_V = 1\text{ V/V}$, Large Signal Behavior (1 V/div, 2 $\mu\text{s/div}$)

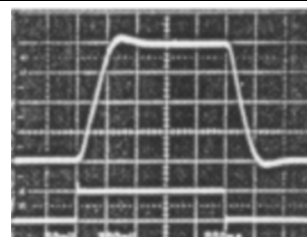
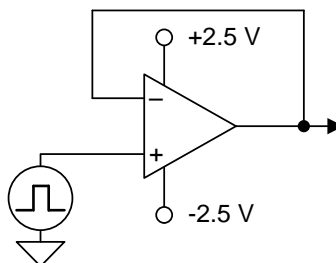


Figure 23. $A_V = 1\text{ V/V}$, Small Signal Behavior (0.2 V/div, 200 $\mu\text{s/div}$)



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Figure 24. $A_V = 1\text{-V/V}$ Schematic

7.2.3 Wide Supply Range

The high power-supply rejection ratio (PSRR) and common-mode rejection ratio (CMRR) provide precision performance when operated on battery or other unregulated supplies. This advantage is further enhanced by the very wide supply range (2.2 V to 30 V, ensured) offered by the LM7301. In situations where highly variable or unregulated supplies are present, the excellent PSRR and wide supply range of the LM7301 benefit the system designer with continued precision performance, even in such adverse supply conditions.

7.2.4 Specific Advantages of 5-Pin SOT-23 (TinyPak)

The obvious advantage of the 5-pin SOT-23, TinyPak, is that it can save board space, a critical aspect of any portable or miniaturized system design. The need to decrease overall system size is inherent in any handheld, portable, or lightweight system application.

Furthermore, the low profile can help in height limited designs, such as consumer hand-held remote controls, sub-notebook computers, and PCMCIA cards.

An additional advantage of the tiny package is that it allows better system performance due to ease of package placement. Because the tiny package is so small, it can fit on the board right where the operational amplifier must be placed for optimal performance, unconstrained by the usual space limitations. This optimal placement of the tiny package allows for many system enhancements that are not easily achieved with the constraints of a larger package. For example, problems such as system noise due to undesired pickup of digital signals can be easily reduced or mitigated. This pickup problem is often caused by long wires in the board layout going to or from an operational amplifier. By placing the tiny package closer to the signal source and allowing the LM7301 output to drive the long wire, the signal becomes less sensitive to such pickup. An overall reduction of system noise results.

Often times system designers try to save space by using dual or quad op amps in their board layouts. This causes a complicated board layout due to the requirement of routing several signals to and from the same place on the board. Using the tiny operational amplifier eliminates this problem.

Additional space savings parts are available in tiny packages from Texas Instruments, including low-power amplifiers, precision-voltage references, and voltage regulators.

Feature Description (continued)

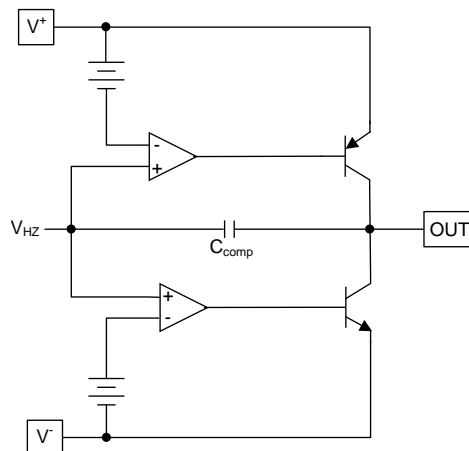
7.2.5 Low-Distortion, High-Output Drive Capability

The LM7301 offers superior low-distortion performance, with a total-harmonic-distortion-plus-noise of 0.06% at $f = 10$ kHz. The advantage offered by the LM7301 is its low distortion levels, even at high output current and low load resistance. See [Stability Considerations](#) for methods used to ensure stability under all load conditions.

7.3 Device Functional Modes

7.3.1 Stability Considerations

Rail-to-rail output amplifiers like the LM7301 use the collector of the drive transistor(s) at the output pin, as shown in [Figure 25](#). This allows the load to be driven as close as possible towards either supply rail.

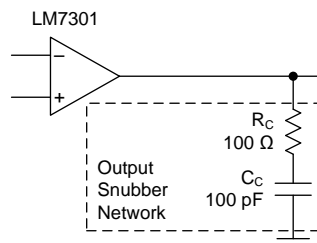


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Figure 25. Simplified Output Stage Block Diagram

While this architecture maximizes the load voltage swing range, it increases the dependence of loop gain and subsequently stability, on load impedance and DC load current, compared to a non-rail-to-rail architecture. Thus, with this type of output stage, it is even more crucial to ensure stability by meticulous bench verification under all load conditions, and to apply the necessary compensation or circuit modifications to overcome any instability, if necessary. Any such bench verification should also include temperature, supply voltage, input common mode and output bias point variations as well as capacitive loading.

For example, one set of conditions for which stability of the LM7301 amplifier may be compromised is when the DC output load is larger than ± 0.5 mA, with input and output biased to mid-rail. Under such conditions, it may be possible to observe open-loop gain response peaking at a high frequency (for example, 200 MHz), which is beyond the expected frequency range of the LM7301 (4 MHz GBW). Without taking any precautions against gain peaking, it is possible to see increased settling time or even oscillations, especially with low closed loop gain and / or light AC loading. It is possible to reduce or eliminate this gain peaking by using external compensation components. One possible scheme that can be applied to reduce or eliminate this gain peaking is shown in [Figure 26](#).



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Figure 26. Non-Dissipating Snubber Network to Reduce Gain Peaking

Device Functional Modes (continued)

The non-dissipating snubber, consisting of R_c and C_c , acts as AC load to reduce high-frequency gain peaking with no DC loading so that total power dissipation is not increased. The increased AC load effectively reduces loop gain at higher frequencies thereby reducing gain peaking due to the possible causes stated in the previous sentence. For the particular set of R_c and C_c values shown in [Figure 26](#), loop gain peaking is reduced by about 25 dB under worst case peaking conditions ($I_{source} = 2\text{mA DC}$ at around 180 MHz) thus confining loop gain to less than 0 dB and eliminating any possible instability. For best results, it may be necessary to *tune* the values of R_c and C_c in a particular application to consider other subtleties and tolerances.

7.3.2 Power Dissipation

Although the LM7301 has internal output current limiting, shorting the output to ground when operating on a 30-V power supply will cause the operational amplifier to dissipate about 350 mW. This is a worst-case example. In the 8-pin SOIC package, this will cause a temperature rise of 42°C. In the 5-pin SOT-23 package, the higher thermal resistance will cause a calculated rise of 59°C. This can raise the junction temperature to greater than the absolute maximum temperature of 150°C.

Operating from split supplies greatly reduces the power dissipated when the output is shorted. Operating on $\pm 15\text{-V}$ supplies can only cause a temperature rise of 21°C in the 8-pin SOIC and 30°C in the 5-pin SOT-23 package, assuming the short is to ground.

8 Applications and Implementation

NOTE

Information in the following applications sections is not part of the TI component specification, and TI does not warrant its accuracy or completeness. TI's customers are responsible for determining suitability of components for their purposes. Customers should validate and test their design implementation to confirm system functionality.

8.1 Application Information

8.1.1 Handheld Remote Controls

The LM7301 offers outstanding specifications for applications requiring good speed/power trade-off. In applications such as remote control operation, where high bandwidth and low power consumption are needed, the LM7301 performance can easily meet these requirements.

8.1.2 Remote Microphone in Personal Computers

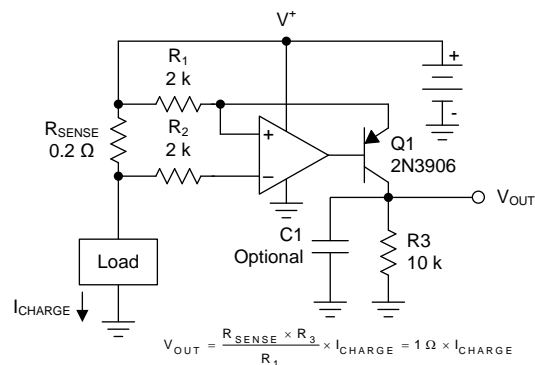
Remote microphones in Personal Computers often use a microphone at the top of the monitor which must drive a long cable in a high noise environment. One method often used to reduce the noise is to lower the signal impedance, which reduces the noise pickup. In this configuration, the amplifier usually requires 30 db to 40 db of gain, at bandwidths higher than most low-power CMOS parts can achieve. The LM7301 offers the tiny package, higher bandwidths, and greater output drive capability than other rail-to-rail input/output parts can provide for this application.

8.1.3 Optical Line Isolation for Modems

The combination of the low distortion and good load driving capabilities of the LM7301 make it an excellent choice for driving opto-coupler circuits to achieve line isolation for modems. This technique prevents telephone line noise from coupling onto the modem signal. Superior isolation is achieved by coupling the signal optically from the computer modem to the telephone lines; however, this also requires a low distortion at relatively high currents. Due to its low distortion at high-output drive currents, the LM7301 fulfills this need, in this and in other telecom applications. See [Stability Considerations](#) for methods used to ensure stability under all load conditions.

8.2 Typical Applications

The circuit shown in [Figure 27](#) uses the wide supply voltage range (1.8 V to 32 V), rail-to-rail input and output voltage capability, and the unity gain stability of the LM7301 to sense the current flow from the power supply to a load, such as a battery being charged, or any other load. The circuit creates a ground-referenced output voltage, which varies linearly with the load current, for easy interface to the rest of the circuitry to create fault-protection, current and power metering, or current regulation functions.



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Figure 27. High Side Current Sensing

Typical Applications (continued)

8.2.1 Design Requirements

The output port is designed for easy interface; it is ground-referenced and it produces 0 V with 0 A of load current. A typical stage that follows this stage, an ADC which samples the load current for example, is easily connected to the Q1 collector with no level shifting or additional biasing required.

Apart from a wide supply voltage capability, the operational amplifier used in [Figure 27](#) must have an input voltage range that includes the V+ rail voltage to allow *high side* current sensing. Furthermore, it should be unity gain stable and have an output voltage range which is less than one V_{be} from V+. The LM7301 has all these requirements.

8.2.2 Detailed Design Procedure

8.2.2.1 Selecting R_{SENSE}

Pick the value of R_{SENSE} low enough to minimize its heat / voltage loss while observing [Equation 1](#) for minimum detectable load current, I_{CHARGE_MIN} , and device offset voltage, V_{OS} :

$$R_{SENSE} > \frac{V_{OS}}{I_{CHARGE_MIN}} \quad (1)$$

With the schematic values shown and LM7301's V_{OS} limit of 6 mV:

$$I_{CHARGE_MIN} > 30 \text{ mA} \quad (2)$$

If the system has the ability to be initialized and corrected for initial readings, it may be possible to lower the value of R_{SENSE} .

8.2.2.2 Selecting $R1$, and $R3$ Values

Pick the $R3 / R1$ ratio to get the proper full-scale V_{OUT} when the maximum load current, I_{CHARGE_MAX} , flows:

$$\frac{R3}{R1} = \frac{V_{OUT}}{R_{SENSE} \times I_{CHARGE_MAX}} \quad (3)$$

For example, to get 3-V output with 3 A of load current when $R_{SENSE} = 0.2 \Omega$ results in:

$$\frac{R3}{R1} = 5 \quad (4)$$

Ensure that the resulting transfer function also satisfies the application's need when the minimum load current, I_{CHARGE_MIN} is being sensed. In this example, the minimum output voltage will be 30 mV (when $I_{CHARGE_MIN} = 30 \text{ mA}$).

With the $R3/R1$ ratio determined, pick the value of $R3$ for Q1 collector current less than 1 mA at the maximum V_{OUT} , and determine $R1$ from that.

8.2.2.3 $R1$, $R2$ Selection

Normally, $R2$ is set equal to $R1$ to cancel out the error term due to the input bias current, I_B (approximately 200 nA for the LM7301).

8.2.2.4 Error Terms Expressions

Here are the expressions for the output change caused by various parameter shifts, evaluated for [Figure 27](#) values with $I_{CHARGE_MAX} = 3 \text{ A}$:

Offset Voltage, ΔV_{OS} :

$$\Delta V_{OUT} = \frac{\Delta V_{OS} \times R3}{R1} = 5 \Delta V_{OS} \quad (5)$$

Offset current, I_{OS} :

$$\Delta V_{OUT} = \frac{\Delta I_{OS} \times R2 \times R3}{R1} = I_{OS} \times 10 \text{ k} \quad (6)$$

Typical Applications (continued)

Self-heating of R_{SENSE} causing ΔR_{SENSE} with I_{CHARGE_MAX} flowing:

$$\Delta V_{OUT} = \Delta R_{SENSE} \times I_{CHARGE_MAX} \times \frac{R3}{R1} = \Delta R_{SENSE} \times 15 \tag{7}$$

8.2.2.5 Frequency Response

Depending on the application, it may be useful to have the means to control the upper end of the circuit's frequency response. An example is limiting the circuit's response to high-frequency load current spikes or switching frequencies so that the circuit only reacts to DC or lower frequencies. Capacitor C1 in Figure 27 can be used to accomplish just that. The original circuit has a -3-dB bandwidth close to 4.5 MHz which can be reduced by increasing the value of C1, as shown in Figure 28.

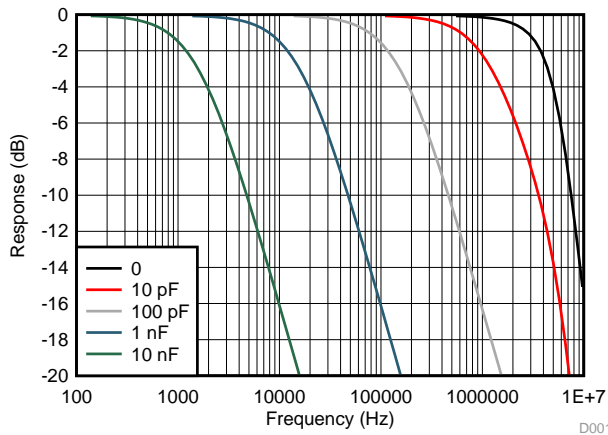


Figure 28. Current Sense Frequency Response vs C1 Value

8.2.3 Application Curves

Figure 29 shows the transfer function of the circuit for several values of R_{SENSE} . Notice that with 1 Ω , the output is limited to approximately 16 V because of the additional drop across the sense resistor at higher load currents.

Figure 30 shows the low-end of the load current is more non-linear for low R_{SENSE} values, as noted in *Selecting R_{SENSE}* due to V_{OS} . Higher R_{SENSE} values help with this at the expense of a higher loss and voltage drop.

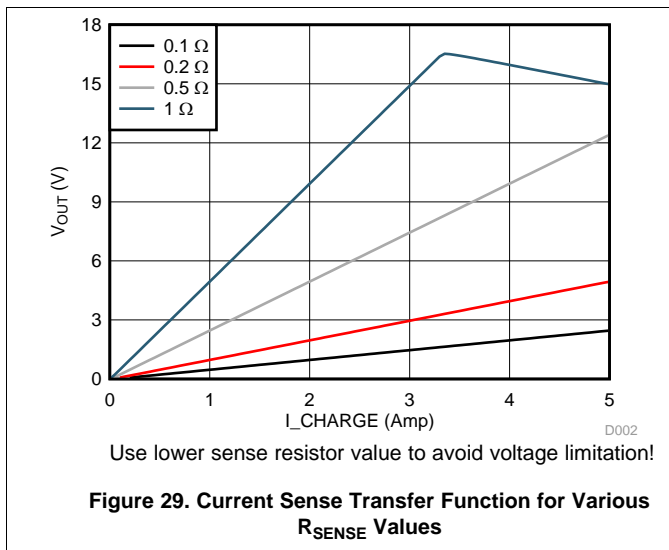


Figure 29. Current Sense Transfer Function for Various R_{SENSE} Values

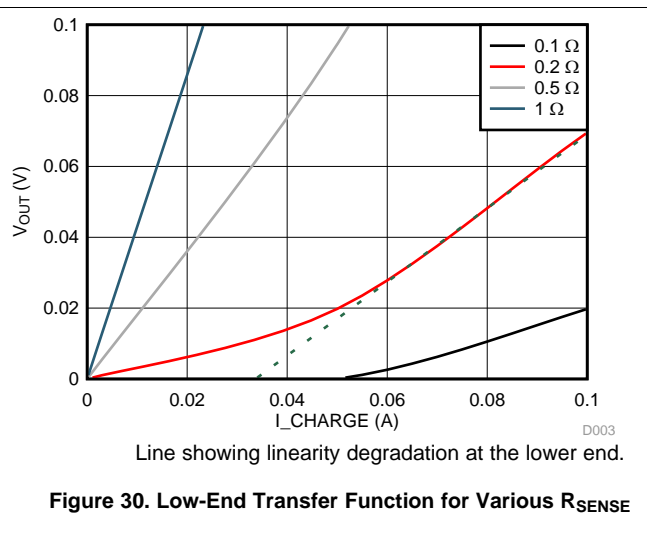


Figure 30. Low-End Transfer Function for Various R_{SENSE}

9 Power Supply Recommendations

The LM7301 is specified for operation from 1.8 V to 32 V (± 0.9 V to ± 16 V). Being a rail-to-rail input and output device, any operating voltage conditions within the supply voltage range can be accommodated.

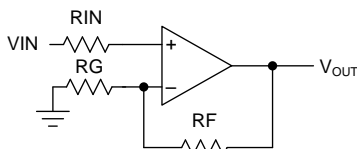
Place 0.1- μ F bypass capacitors close to the power-supply pins to reduce errors coupling in from noisy or high-impedance power supplies.

10 Layout

10.1 Layout Guidelines

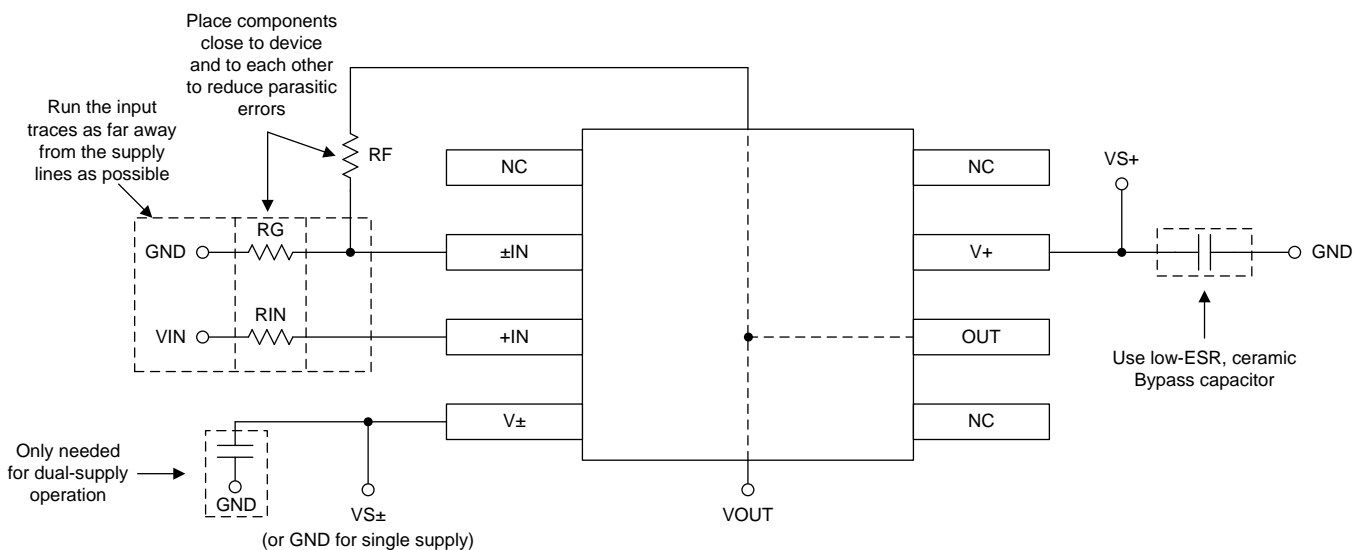
For best operational performance of the device, TI recommends good printed-circuit board (PCB) layout practices. Low-loss, 0.1- μ F bypass capacitors should be connected between each supply pin and ground, placed as close to the device as possible. A single bypass capacitor from V+ to ground is applicable to single supply applications.

10.2 Layout Example



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Figure 31. Schematic Representation



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Figure 32. Operational Amplifier Board Layout for Noninverting Configuration

11 デバイスおよびドキュメントのサポート

11.1 コミュニティ・リソース

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Design Support *TI's Design Support* Quickly find helpful E2E forums along with design support tools and contact information for technical support.

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11.4 Glossary

SLYZ022 — *TI Glossary*.

This glossary lists and explains terms, acronyms, and definitions.

12 メカニカル、パッケージ、および注文情報

以降のページには、メカニカル、パッケージ、および注文に関する情報が記載されています。これらの情報は、指定のデバイスに対して提供されている最新のデータです。このデータは予告なく変更されることがあり、ドキュメントが改訂される場合もあります。本データシートのブラウザ版を使用されている場合は、画面左側の説明をご覧ください。

PACKAGING INFORMATION

Orderable Device	Status (1)	Package Type	Package Drawing	Pins	Package Qty	Eco Plan (2)	Lead finish/ Ball material (6)	MSL Peak Temp (3)	Op Temp (°C)	Device Marking (4/5)	Samples
LM7301IM5/NOPB	ACTIVE	SOT-23	DBV	5	1000	RoHS & Green	NIPDAU SN	Level-1-260C-UNLIM	-40 to 85	A04A	Samples
LM7301IM5X/NOPB	ACTIVE	SOT-23	DBV	5	3000	RoHS & Green	NIPDAU SN	Level-1-260C-UNLIM	-40 to 85	A04A	Samples
LM7301IMX/NOPB	ACTIVE	SOIC	D	8	2500	RoHS & Green	NIPDAU SN	Level-1-260C-UNLIM	-40 to 85	LM73 01IM	Samples

(1) The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

OBSOLETE: TI has discontinued the production of the device.

(2) **RoHS:** TI defines "RoHS" to mean semiconductor products that are compliant with the current EU RoHS requirements for all 10 RoHS substances, including the requirement that RoHS substance do not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, "RoHS" products are suitable for use in specified lead-free processes. TI may reference these types of products as "Pb-Free".

RoHS Exempt: TI defines "RoHS Exempt" to mean products that contain lead but are compliant with EU RoHS pursuant to a specific EU RoHS exemption.

Green: TI defines "Green" to mean the content of Chlorine (Cl) and Bromine (Br) based flame retardants meet JS709B low halogen requirements of <=1000ppm threshold. Antimony trioxide based flame retardants must also meet the <=1000ppm threshold requirement.

(3) MSL, Peak Temp. - The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

(4) There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.

(5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.

(6) Lead finish/Ball material - Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

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TAPE AND REEL INFORMATION

QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE


*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
LM7301IM5/NOPB	SOT-23	DBV	5	1000	178.0	8.4	3.2	3.2	1.4	4.0	8.0	Q3
LM7301IM5/NOPB	SOT-23	DBV	5	1000	180.0	8.4	3.2	3.2	1.4	4.0	8.0	Q3
LM7301IM5X/NOPB	SOT-23	DBV	5	3000	180.0	8.4	3.2	3.2	1.4	4.0	8.0	Q3
LM7301IM5X/NOPB	SOT-23	DBV	5	3000	178.0	8.4	3.2	3.2	1.4	4.0	8.0	Q3
LM7301IMX/NOPB	SOIC	D	8	2500	330.0	12.4	6.5	5.4	2.0	8.0	12.0	Q1

TAPE AND REEL BOX DIMENSIONS


*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
LM7301IM5/NOPB	SOT-23	DBV	5	1000	208.0	191.0	35.0
LM7301IM5/NOPB	SOT-23	DBV	5	1000	210.0	185.0	35.0
LM7301IM5X/NOPB	SOT-23	DBV	5	3000	210.0	185.0	35.0
LM7301IM5X/NOPB	SOT-23	DBV	5	3000	208.0	191.0	35.0
LM7301IMX/NOPB	SOIC	D	8	2500	367.0	367.0	35.0

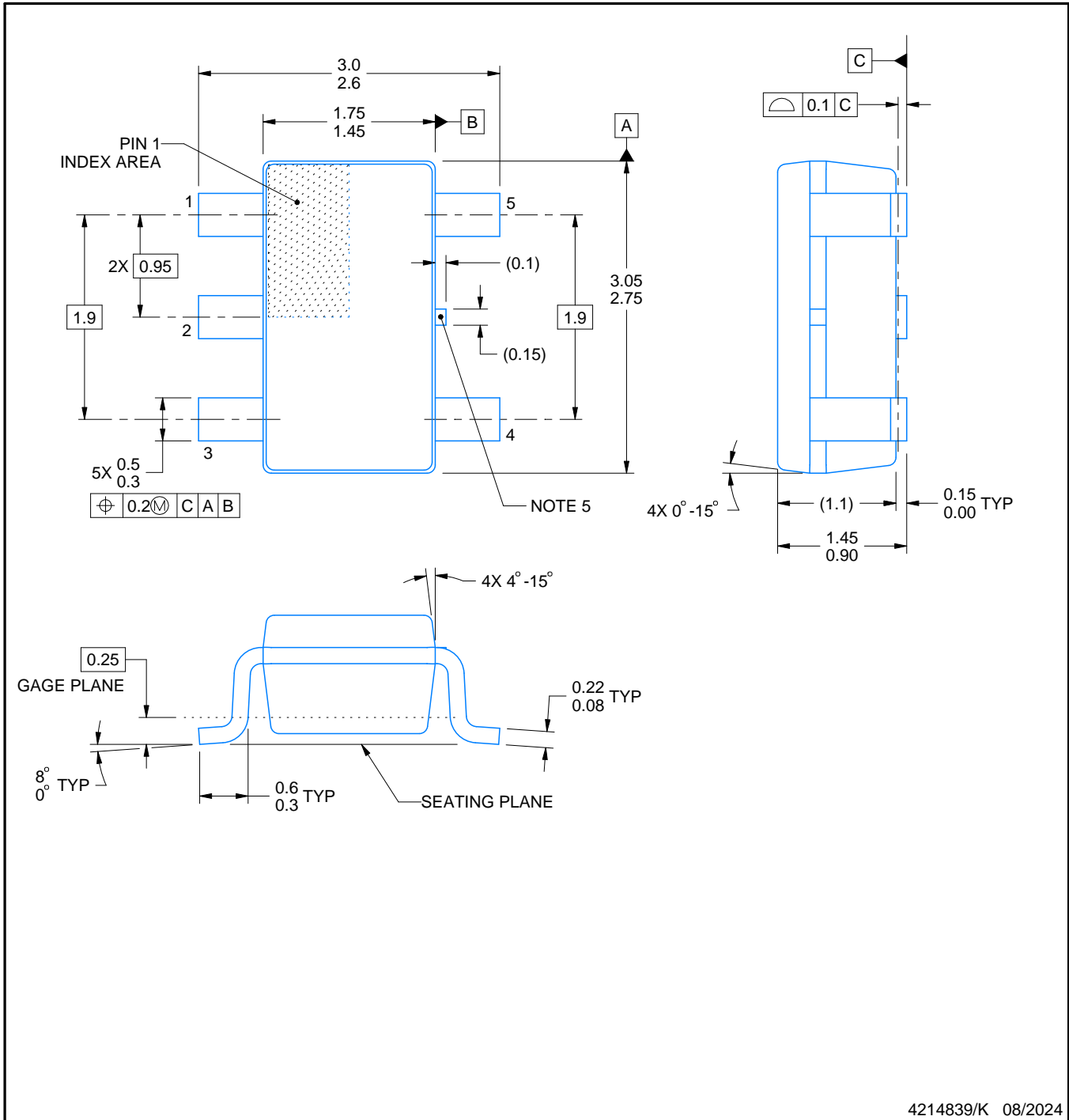
DBV0005A



PACKAGE OUTLINE

SOT-23 - 1.45 mm max height

SMALL OUTLINE TRANSISTOR



NOTES:

1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
2. This drawing is subject to change without notice.
3. Reference JEDEC MO-178.
4. Body dimensions do not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0.25 mm per side.
5. Support pin may differ or may not be present.

EXAMPLE BOARD LAYOUT

DBV0005A

SOT-23 - 1.45 mm max height

SMALL OUTLINE TRANSISTOR



LAND PATTERN EXAMPLE
EXPOSED METAL SHOWN
SCALE:15X



SOLDER MASK DETAILS

4214839/K 08/2024

NOTES: (continued)

- 6. Publication IPC-7351 may have alternate designs.
- 7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.

EXAMPLE STENCIL DESIGN

DBV0005A

SOT-23 - 1.45 mm max height

SMALL OUTLINE TRANSISTOR



SOLDER PASTE EXAMPLE
BASED ON 0.125 mm THICK STENCIL
SCALE:15X

4214839/K 08/2024

NOTES: (continued)

8. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
9. Board assembly site may have different recommendations for stencil design.



D0008A

PACKAGE OUTLINE

SOIC - 1.75 mm max height

SMALL OUTLINE INTEGRATED CIRCUIT



4214825/C 02/2019

NOTES:

1. Linear dimensions are in inches [millimeters]. Dimensions in parenthesis are for reference only. Controlling dimensions are in inches. Dimensioning and tolerancing per ASME Y14.5M.
2. This drawing is subject to change without notice.
3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed $.006$ [0.15] per side.
4. This dimension does not include interlead flash.
5. Reference JEDEC registration MS-012, variation AA.

EXAMPLE BOARD LAYOUT

D0008A

SOIC - 1.75 mm max height

SMALL OUTLINE INTEGRATED CIRCUIT



LAND PATTERN EXAMPLE
EXPOSED METAL SHOWN
SCALE:8X



SOLDER MASK DETAILS

4214825/C 02/2019

NOTES: (continued)

6. Publication IPC-7351 may have alternate designs.

7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.

EXAMPLE STENCIL DESIGN

D0008A

SOIC - 1.75 mm max height

SMALL OUTLINE INTEGRATED CIRCUIT



SOLDER PASTE EXAMPLE
BASED ON .005 INCH [0.125 MM] THICK STENCIL
SCALE:8X

4214825/C 02/2019

NOTES: (continued)

8. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
9. Board assembly site may have different recommendations for stencil design.

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